

Amendments to the Specification:

Please amend the paragraph beginning on page 3, line 25 to read as follows:

The second dielectric layer 1003 and the third dielectric layer 1006 have a function of preventing mass transfer from being caused between the first dielectric layer 1002 and the recording layer 1005 and between the fourth dielectric layer 1007 and the recording layer 1005. The mass transfer is a phenomenon caused when $(\text{ZnS})_{80}(\text{SiO}_2)_{20}$ (mol%) is used for each of the first dielectric layer 1002 and the fourth dielectric layer 1007. In this phenomenon, when recording/rewriting is performed repeatedly by irradiation of laser beams to the recording layer 1005, S is diffused in the recording layer 1005. When S is diffused in the recording layer 1005, the repeated rewriting capability is deteriorated (see, for example, N. Yamada et al., Japanese Journal of Applied Physics, Vol. 37 (1998), pp. 2104-2110). In order to prevent the deterioration in repeated rewriting capability, a nitride containing Ge should be used for the second dielectric layer 1003 and the third dielectric layer 1006 (see, for example, ~~JP 9(1997)-532424 A~~ WO 97-34298 and ~~JP 9(1997)-79477 A~~ JP 10 (1998)-275360).